

# **4V Drive Pch MOSFET**

#### RT1E050RP

#### Structure

Silicon P-channel MOSFET

#### Features

- 1) Low on-resistance.
- 2) High power package.
- 3) 4V drive.

#### Application

Switching

#### Packaging specifications

	Package	Taping	
Type	Code	TR	
	Basic ordering unit (pieces)	3000	
RT1E050RP		0	

#### ● Absolute maximum ratings (Ta = 25°C)

Parameter		Symbol	Limits	Unit
Drain-source voltage		$V_{DSS}$	-30	V
Gate-source voltage		$V_{GSS}$	±20	V
Drain current	Continuous	I <sub>D</sub>	±5	Α
Diam current	Pulsed	I <sub>DP</sub> *1	±20	Α
Source current	Continuous	I <sub>S</sub>	-1	Α
(Body Diode)	Pulsed	I <sub>SP</sub> *1	-20	Α
Power dissipation		P <sub>D</sub> *2	1.25	W
Channel temperature		Tch	150	°C
Range of storage temperature		Tstg	-55 to +150	°C

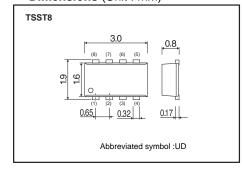
<sup>\*1</sup> Pw≤10µs, Duty cycle≤1%

#### Thermal resistance

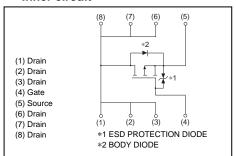
Parameter	Symbol	Limits	Unit
Channel to Ambient	Rth (ch-a)*	100	°C/W

<sup>\*</sup>Mounted on a ceramic board.

#### • Dimensions (Unit : mm)



#### • Inner circuit



<sup>\*2</sup> Mounted on a ceramic board.

#### ● Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	$I_{GSS}$	-	-	±10	μA	$V_{GS}=\pm20V$ , $V_{DS}=0V$
Drain-source breakdown voltage	$V_{(BR)DSS}$	-30	-	-	V	$I_D=-1$ mA, $V_{GS}=0$ V
Zero gate voltage drain current	I <sub>DSS</sub>	ı	-	-1	μA	$V_{DS}$ =-30V, $V_{GS}$ =0V
Gate threshold voltage	V <sub>GS (th)</sub>	-1.0	-	-2.5	V	$V_{DS}$ =-10V, $I_{D}$ =-1mA
Chatia duain accuracy and at-	*	ı	26	36		I <sub>D</sub> =-5A, V <sub>GS</sub> =-10V
Static drain-source on-state resistance	R <sub>DS (on)</sub>	1	36	50	mΩ	$I_D = -2.5A, V_{GS} = -4.5V$
		ı	40	56		I <sub>D</sub> =-2.5A, V <sub>GS</sub> =-4.0V
Forward transfer admittance	IY <sub>fs</sub> ľ	3.1	-	-	S	$I_D = -5A, V_{DS} = -10V$
Input capacitance	C <sub>iss</sub>	ı	1300	-	pF	V <sub>DS</sub> =-10V
Output capacitance	C <sub>oss</sub>	ı	180	-	pF	V <sub>GS</sub> =0V
Reverse transfer capacitance	C <sub>rss</sub>	1	160	-	pF	f=1MHz
Turn-on delay time	t <sub>d(on)</sub> *	1	10	-	ns	I <sub>D</sub> =-2.5A, V <sub>DD</sub> ≒-15V
Rise time	t <sub>r</sub> *	ı	15	-	ns	V <sub>GS</sub> =-10V
Turn-off delay time	t <sub>d(off)</sub> *	-	90	-	ns	$R_L=6.0\Omega$
Fall time	t <sub>f</sub> *	-	50	-	ns	$R_G=10\Omega$
Total gate charge	Q <sub>g</sub> *	-	13	-	nC	I <sub>D</sub> =-5A, V <sub>D</sub> 15V
Gate-source charge	Q <sub>gs</sub> *	-	3.5	-	nC	$V_{GS}=-5V R_L=3\Omega$
Gate-drain charge	Q <sub>gd</sub> *	-	4.5	-	nC	$R_G=10\Omega$

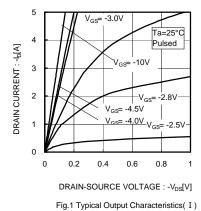
<sup>\*</sup>Pulsed

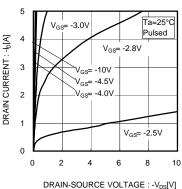
### ●Body diode characteristics (Source-Drain) (Ta = 25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward Voltage	$V_{SD}^{*}$	-	-	-1.2	V	$I_s=-5A$ , $V_{GS}=0V$

<sup>\*</sup>Pulsed

#### • Electrical characteristics curves





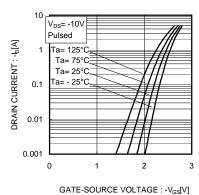
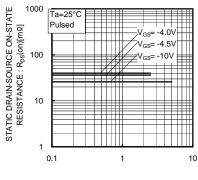


Fig.2 Typical Output Characteristics( II)

Fig.3 Typical Transfer Characteristics



DRAIN-CURRENT : -Ы[A]
Fig.4 Static Drain-Source On-State
Resistance vs. Drain Current( I )

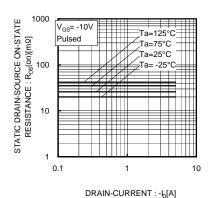


Fig.5 Static Drain-Source On-State
Resistance vs. Drain Current( II )

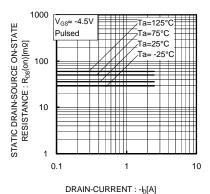


Fig.6 Static Drain-Source On-State Resistance vs. Drain Current(Ⅲ)

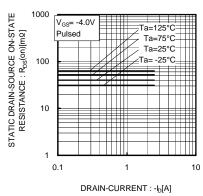


Fig.7 Static Drain-Source On-State Resistance vs. Drain Current(IV)

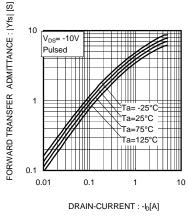


Fig.8 Forward Transfer Admittance vs. Drain Current

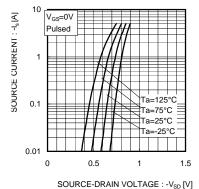


Fig.9 Reverse Drain Current vs. Sourse-Drain Voltage

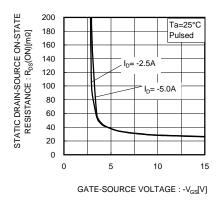


Fig.10 Static Drain-Source On-State
Resistance vs. Gate Source Voltage

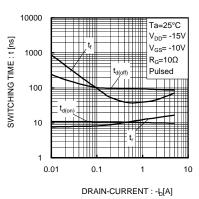


Fig.11 Switching Characteristics

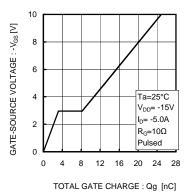


Fig.12 Dynamic Input Characteristics

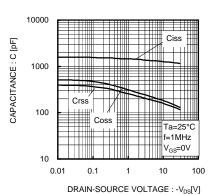


Fig.13 Typical Capacitance vs. Drain-Source Voltage

#### Measurement circuits

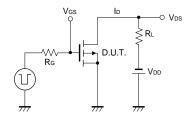


Fig.1-1 Switching Time Measurement Circuit

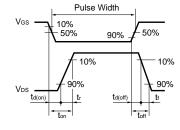


Fig.1-2 Switching Waveforms

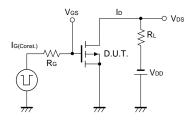


Fig.2-1 Gate Charge Measurement Circuit

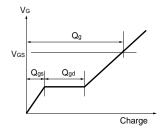


Fig.2-2 Gate Charge Waveform

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**Distribution Inventory** 

Part Number	RT1E050RP
Package	TSST8
Unit Quantity	3000
Minimum Package Quantity	3000
Packing Type	Taping
Constitution Materials List	inquiry
RoHS	Yes

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